BSCP 1207 Physics of Semiconductor Devices

Module-I (10 Hours)

1. **Introduction to the quantum theory of solids**: Formation of energy bands, The k-space diagram (two and three dimensional representation), conductors, semiconductors and insulators.
2. **Electrons and Holes in semiconductors:** Silicon crystal structure, Donors and acceptors in the band model, electron effective mass, Density of states, Thermal equilibrium, Fermi-Dirac distribution function for electrons and holes, Fermi energy. Equilibrium distribution of electrons & holes: derivation of *n* and *p* from D(E) and f(E), Fermi level and carrier concentrations, The *np* product and the intrinsic carrier concentration. General theory of *n* and *p*, Carrier concentrations at extremely high and low temperatures: complete ionization, partial ionization and freeze-out. Energy-band diagram and Fermi-level, Variation of E_F with doping concentration and temperature.
3. **Motion and Recombination of Electrons and Holes:** Carrier drift: Electron and hole mobilities, Mechanism of carrier scattering, Drift current and conductivity.

Module II (11 Hours)

4. **Motion and Recombination of Electrons and Holes (continued):** Carrier diffusion: diffusion current, Total current density, relation between the energy diagram and potential, electric field. Einstein relationship between diffusion coefficient and mobility. Electron-hole recombination, Thermal generation.
5. **PN Junction:** Building blocks of the pn junction theory: Energy band diagram and depletion layer of a pn junction, Built-in potential; Depletion layer model: Field and potential in the depletion layer, depletion-layer width; Reverse-biased PN junction; Capacitance-voltage characteristics; Junction breakdown: peak electric field. Tunneling breakdown and avalanche breakdown; Carrier injection under forward bias-Quasi-equilibrium boundary condition; current continuity equation; Excess carriers in forward-biased pn junction; PN diode I-V characteristic, Charge storage.
6. **The Bipolar Transistor:** Introduction, Modes of operation, Minority Carrier distribution, Collector current, Base current, current gain, Base width Modulation by collector current, Breakdown mechanism, Equivalent Circuit Models - Ebers -Moll Model.

Module III (12 Hours)

7. **Metal-Semiconductor Junction:** Schottky Diodes: Built-in potential, Energy-band diagram, I-V characteristics, Comparison of the Schottky barrier diode and the pn-junction diode. Ohmic contacts: tunneling barrier, specific contact resistance**.**
8. **MOS Capacitor:** The MOS structure, Energy band diagrams, Flat-band condition and flat-band voltage, Surface accumulation, surface depletion, Threshold condition and threshold voltage, MOS C-V characteristics, Q_{inv} in MOSFET.
9. **MOS Transistor:** Introduction to the MOSFET, Complementary MOS (CMOS) technology, V-I Characteristics, Surface mobilities and high-mobility FETs, JFET, MOSFET V_t, Body effect and steep retrograde doping, pinch-off voltage,

Text Books:

1. Modern Semiconductor Devices for Integrated Circuits, Chenming Calvin Hu, Pearson Education/Prentice Hall, 2009.
2. Semiconductor Physics and Devices, 3rd Edition, Donald A. Neamen, Tata McGraw Hill Publishing Company Limited, New Delhi.

Reference Books:

1. Fundamentals of Semiconductor Devices, M.K. Achuthan and K.N. Bhatt, Tata McGraw Hill Publishing Company Limited, New Delhi.
2. Solid State Electronics Devices, 6th Edition, Ben. G. Stretman and Sanjay Banarjee, Pearson Education, New Delhi.
3. Physics of Semiconductor Devices, 3rd Edition, S.M. Sze and Kwok K. Ng, Wiley India Pvt. Limited, New Delhi.
4. Physics of Semiconductor Devices, 2nd Edition, Dillip K. Roy, University Press (India) Pvt. Ltd., Hyderabad.
5. Solid State Electronics Devices, D.K. Bhattacharya and Rajnish Sharma, Oxford University Press, New Delhi.